

Abstract

Method for depositing an epitaxial layer on a substrate wafer

- 5 Method for depositing an epitaxial layer on a substrate wafer from a gas phase,
comprising
measuring an edge geometry of the substrate wafer, which assigns a characteristic
thickness value to an edge of the substrate wafer as a function of edge positions,
including the characteristic thickness value at a notch position;
10 placing the substrate wafer on a placement area of a pocket of a susceptor of an
apparatus for depositing the epitaxial layer, the placement area being surrounded by
an outer boundary;
heating the substrate wafer; and
passing process gas over the substrate wafer;
15 characterized by
verifying whether the characteristic thickness value at the notch position differs by
more than a percentage limit from the characteristic thickness value at an edge
position having the greatest characteristic thickness value;
placing the substrate wafer on the placement area in such a way that the distance of
20 the substrate wafer from the outer boundary of the placement area is smaller at the
edge position having the greatest characteristic thickness value than at the other edge
positions, provided that the difference is greater than the percentage limit, or in such a
way that the distance of the substrate wafer from the outer boundary of the placement
area is smaller at the notch position than at the other edge positions, provided that the
25 difference is not greater than the percentage limit.

Drawing for the Abstract: Fig. 2